

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re New Patent Application of)
Shinya SASAGAWA et al.)
Japanese Priority Application No. 2002-361924) Attn: Applications
Japanese Priority Date: December 13, 2002) Branch
For: METHOD OF MANUFACTURING A)
SEMICONDUCTOR DEVICE) Date: December 10, 2003

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

In accordance with the duty of disclosure as set forth in 37 C.F.R. §1.56, Applicants hereby submit the following information in conformance with 37 C.F.R. §§ 1.97 and 1.98. Pursuant to 37 C.F.R. § 1.98, a copy of each of the documents cited is enclosed.

Japanese Patent Application Laid-Open No. 2000-294787 is in the same family as U.S. Patent 6,235,558.

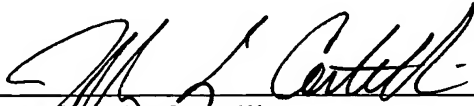
Japanese Patent Application Laid-Open No. 2002-14337 is in the same family as U.S. Patent Publication No. 2001/0035526.

Japanese Patent Application Laid-Open No. 2001-313397 is in the same family as U.S. Patent Publication No. 2001/0030322 and EP Patent No. 1128430.

It is requested that the accompanying PTO-1449 be considered and made of record in the above-identified application. To assist the Examiner, the documents are listed on the attached form PTO-1449. It is respectfully requested

that an Examiner initialed copy of this form be returned to the undersigned.

Respectfully submitted,

By: 
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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>				Complete if Known			
				Application Number		New Application	
				Filing Date		December 10, 2003	
				First Named Inventor		Shinya SASAGAWA et al.	
				Art Unit			
Examiner							
Sheet	1	of	1	Attorney Docket Number		740756-2676	

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	U.S. Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number - Kind Code ² (if known)			
		US-6,235,558 B1	05/22/2001	Oda et al.	
		US-2001/0035526 A1	11/01/2001	Yamazaki et al.	
		US-2001/0030322 A1	10/18/2001	Yamazaki et al.	
		US-4,707-721	11/17/1987	Ang et al.	
		US-5,177,577	01/05/1993	Taniguchi et al.	
		US-5,498,573	03/12/1996	Whetten	
		US-2002/0000551 A1	01/03/2002	Yamazaki et al.	
		US-2001/0052950 A1	12/20/2001	Yamazaki et al.	
		US-2001/0055841 A1	12/27/2001	Yamazaki et al.	
		US-2002/0048829 A1	04/25/2002	Yamazaki et al.	
		US-4,963,504	10/16/1990	Huang	
		US-5,583,067	12/10/1996	Sanchez	

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Country Code ³ Number ⁴ Kind Code ⁵ (if known)				
		JP 2000-294787	10/20/2000	Oda et al.		Abstract
		JP 2002-14337	01/18/2002	Yamazaki et al.		Abstract
		JP 2001-313397	11/09/2001	Yamazaki et al.		Abstract
		EP 1 128 430 A2	08/29/2001	Yamazaki et al.		Full
		JP 06-53324	02/25/1994	Katayama		Abstract
		JP 10-12605	01/16/1998	Shinohara		Abstract
		JP 2000-269331	09/29/2000	Usami et al.		Abstract
		JP 2003-257950	09/12/2003			Abstract

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
		M. Wittmer et al., "Characteristics of TIN gate metal-oxide-semiconductor field effect transistors", J. Appl. Phys. Vol. 54, No. 3, March 1983, pp. 1423-1428.	

Examiner Signature		Date Considered	
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Applicant's unique citation designation number (optional). ² See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

¹ Applicant's unique citation designation number (optional). ² Applicant is to place a check mark here if English language Translation is attached.